

- L3: (5158) 2 and silicon
- L4: (4747) 3 and (GaN or nitride or (group adj2-nitride))
- L5: (4415) 4 and thickness
- L6: (86) 5 and (thick54 near (oxynitride or Si))
- L7: (1059) 5 and (thick54 near5 (oxynitride or Si))
- L8: (362) 7 and thick54.clm
- L9: (160) 8 and (oxynitride or si\$1NS10\$1).clm
- L10: (160) 8 and (oxynitride.clm. or si\$1NS10\$1.clm)
- L11: (101) 10 and (thick54 near5 (oxynitride or Si))
- L12: (460) 11 and (single layer crystal54)
- L13: (0) 12 and ((group adj2-nitride) or (group adj2-nitride))
- L14: (1) ("5563428").PN
- L15: (2) 11 and (GaN or (gallium near1 nitrided))

11 and (single near) crystals(5)

广 江南

Category	Document ID	Issue Date	Page	Title	Current IP	Current DR	Current DR	Reviewed	Investor	SG	IP
17	US 6661065	20031209	50	Semiconductor device and SOI substrate	257/411	257/347	257/5104		Kuniyuki, Tatsuya et al.	✓	✓
18	US 6538287	20030325	9	Method and structure for stacked DRAM capaci	257/350	257/E21-64	51		Wang, Chen-Jong et al.	✓	✓
19	US 6534390	20030318	9	Salicide method for producing a semiconductor	438/592	257/E21-16	51		Chong, Yung Fu et al.	✓	✓
20	US 6468856	20021022	11	High charge storage density integrated circ	438/240	257/E21-19	37		Wallace, Robert M. et al.	✓	✓
21	US 6429538	20020806	5	Method for making a novel stacked silicon ni	257/797	257/437	257/915		Lin, Shih-Chi	✓	✓
22	US 6362041	20020326	9	Method and structure for stacked DRAM capaci	438/253	257/E21-64	51		Wang, Chen-Jong et al.	✓	✓
23	US 6350675	20020226	15	Integration of silicon-rich material i	438/624	438/637	438/638		Chooi, Simon et al.	✓	✓
24	US 6287962	20010911	5	Method for making a novel stacked silicon ni	438/638	257/E21-23	21		Lin, Shih-Chi	✓	✓
25	US 6274471	20010814	4	Method for making high-aspect-ratio conta	438/597	257/E21-50	71		Huang, Jenn Ming	✓	✓
26	US 6204517	20010320	9	Single electron transistor memory array	257/51	257/204	257/66		Wu, Shye-Lin	✓	✓
27	US 6168989	20010102	11	Process for making new and improved crown-sha	438/293	257/E21-01	91		Chieng, Ming-Hsiung et al.	✓	✓
28	US 6156620	20001209	11	Isolation trench in semiconductor substrates	438/400	257/E21-54	91		Puchner, Helmut et al.	✓	✓
29	US 6140179	20001031	13	Method of forming a crown capacitor for a D	438/254	257/E21-01	21		Chen, Yinan et al.	✓	✓
30	US 6121073	20000919	10	Method for making a fuse structure for imor	438/132	257/E23-15			Huang, Kuo Ching et al.	✓	✓
31	US 6084265	20000704	9	High density shallow trench contactless nonv	257/332	257/314	257/321		Wu, Shye-Lin	✓	✓
32	US 6074908	20000613	11	Process for making turned integrated circuit	438/241	438/239	438/253		Huang, Jenn Ming	✓	✓
33	US 6027801	20000222	16	Magnetic recording	428/332	428/336	428/694		Maro, Tsuyoshi et al.	✓	✓